



PJP100P03

30V P-Channel Enhancement Mode MOSFET

Voltage

-30 V

Current

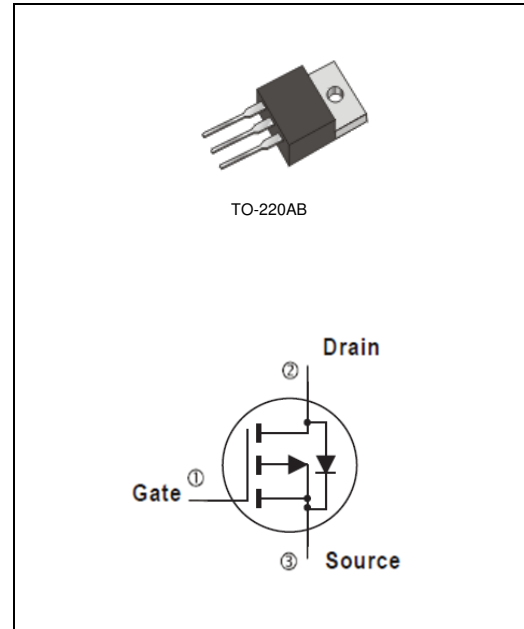
-100 A

Features

- $R_{DS(ON)}$, $V_{GS}@-10V, I_D@-20A < 5m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-4.5V, I_D@-15A < 7.5m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std..
(Halogen Free)

Mechanical Data

- Case : TO-220AB Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0667 ounces, 1.89 grams



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C=25^\circ\text{C}$	I_D	-100	A
	$T_C=100^\circ\text{C}$		-63	
Pulsed Drain Current (Note 1)	$T_C=25^\circ\text{C}$	I_{DM}	-400	
Power Dissipation	$T_C=25^\circ\text{C}$	P_D	119	W
	$T_C=100^\circ\text{C}$		48	
Continuous Drain Current	$T_A=25^\circ\text{C}$	I_D	-15.8	A
	$T_A=70^\circ\text{C}$		-12.6	A
Power Dissipation	$T_A=25^\circ\text{C}$	P_D	2.0	W
Power Dissipation	$T_A=70^\circ\text{C}$		1.3	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	$^\circ\text{C}$
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{\theta JC}$	1.05	$^\circ\text{C/W}$
	Junction to Ambient	$R_{\theta JA}$	62.5	

- Limited only By Maximum Junction Temperature



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Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-30	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.6	-2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-20A	-	3.9	5	mΩ
		V _{GS} =-4.5V, I _D =-15A	-	5.7	7.5	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-	-1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Dynamic (Note 6)						
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-10A, V _{GS} =-10V (Note 2,3)	-	107	-	nC
Gate-Source Charge	Q _{gs}		-	18	-	
Gate-Drain Charge	Q _{gd}		-	18	-	
Input Capacitance	C _{iss}	V _{DS} =-25V, V _{GS} =0V, f=1.0MHZ	-	6067	-	pF
Output Capacitance	C _{oss}		-	709	-	
Reverse Transfer Capacitance	C _{rss}		-	361	-	
Turn-On Delay Time	t _{d(on)}	V _{DS} =-15V, I _D =-1A, V _{GS} =-10V, R _G =6Ω (Note 2,3)	-	22	-	ns
Turn-On Rise Time	t _r		-	48	-	
Turn-Off Delay Time	t _{d(off)}		-	197	-	
Turn-Off Fall Time	t _f		-	90	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I _S	---	-	-	-100	A
Diode Forward Voltage	V _{SD}	I _S =-1A, V _{GS} =0V	-	-0.68	-1	V

NOTES :

1. Pulse width ≤ 300us, Duty cycle ≤ 2%
2. Essentially independent of operating temperature typical characteristics
3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J = 25°C.
4. The maximum current rating is package limited
5. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
6. Guaranteed by design, not subject to production testing



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TYPICAL CHARACTERISTIC CURVES

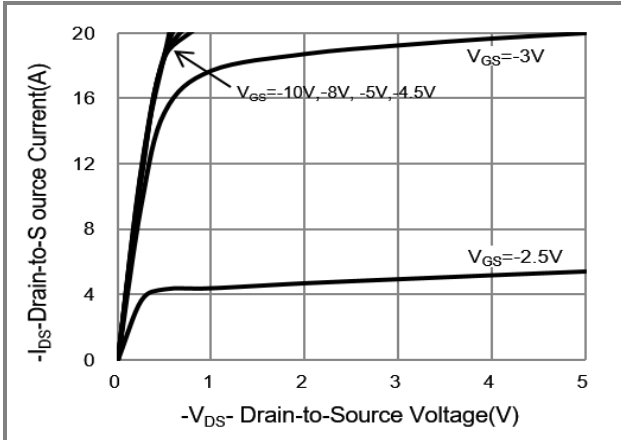


Fig.1 Output Characteristics

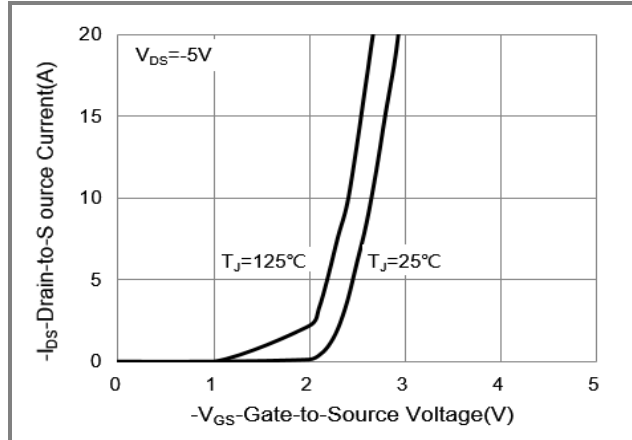


Fig.2 Transfer Characteristics

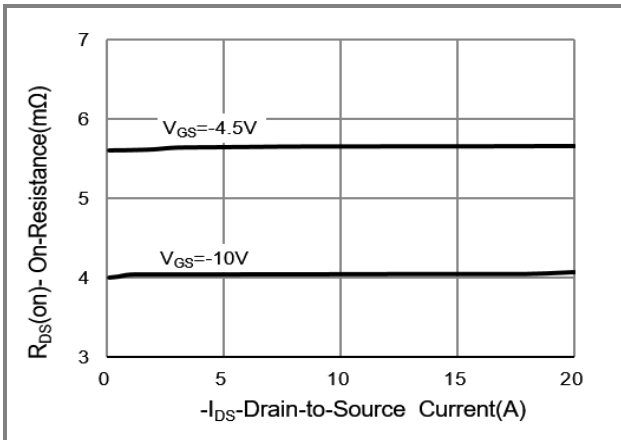


Fig.3 On-Resistance vs. Drain Current

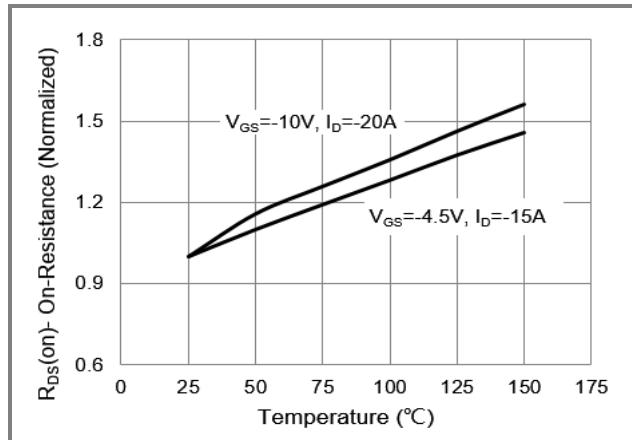


Fig.4 On-Resistance vs. Junction Temperature

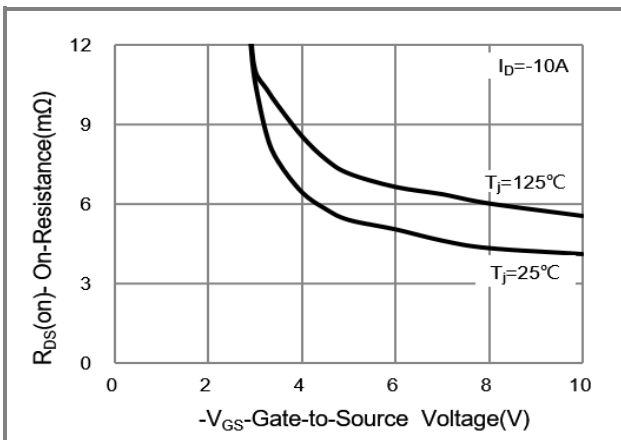


Fig.5 On-Resistance Variation with VGS.

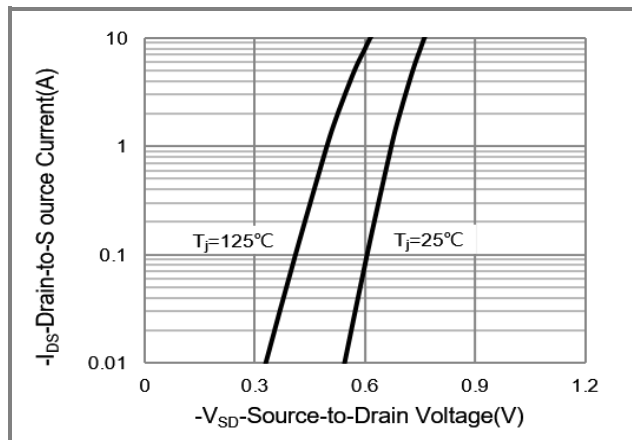


Fig.6 Body Diode Characteristics



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TYPICAL CHARACTERISTIC CURVES

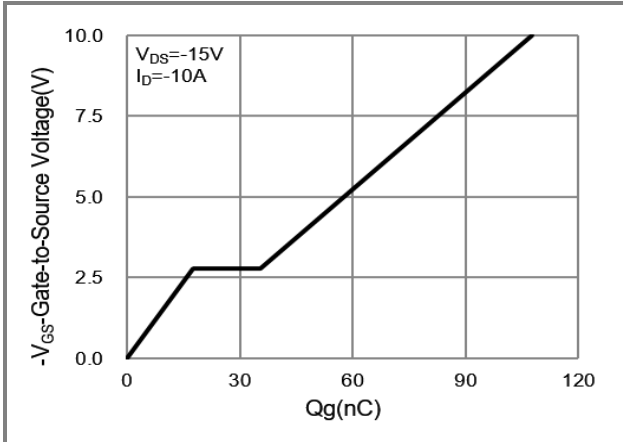


Fig.7 Gate Charge

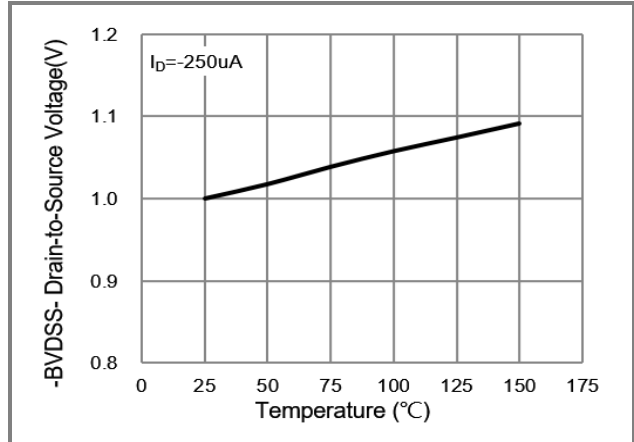


Fig.8 Breakdown Voltage Variation vs. Temperature

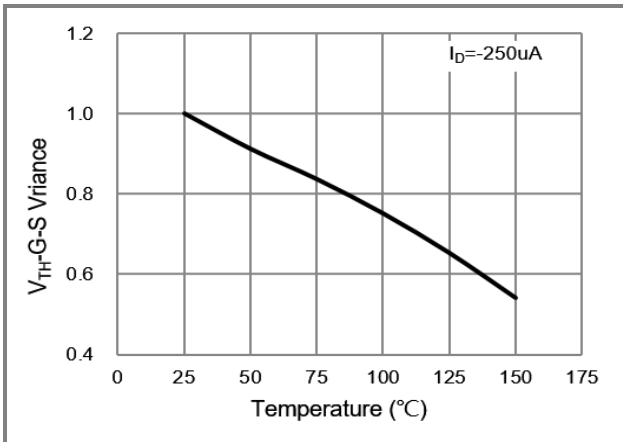


Fig.9 Threshold Voltage Variation with Temperature

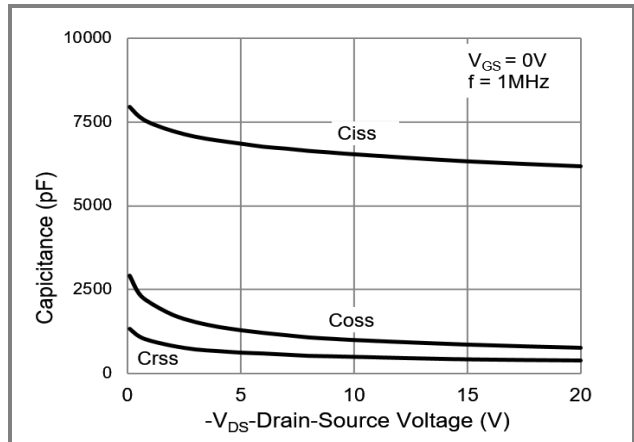


Fig.10 Capacitance vs. Drain-Source Voltage

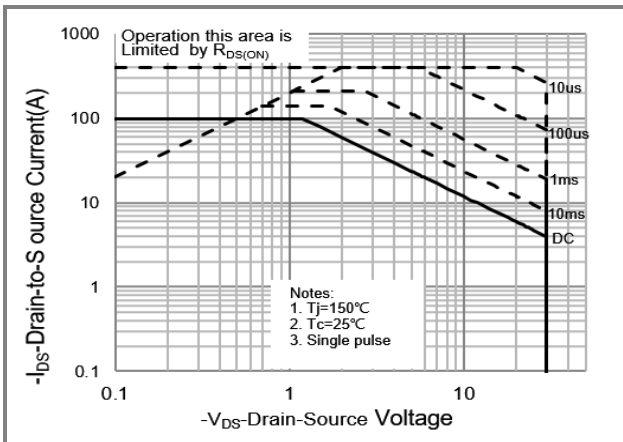


Fig.11 Maximum Safe Operating Area



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TYPICAL CHARACTERISTIC CURVES

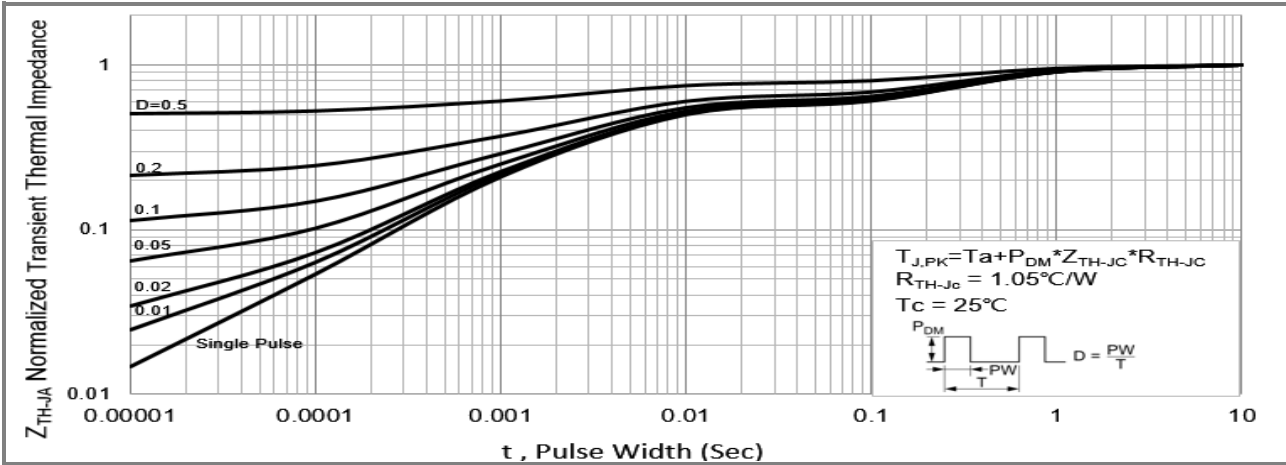
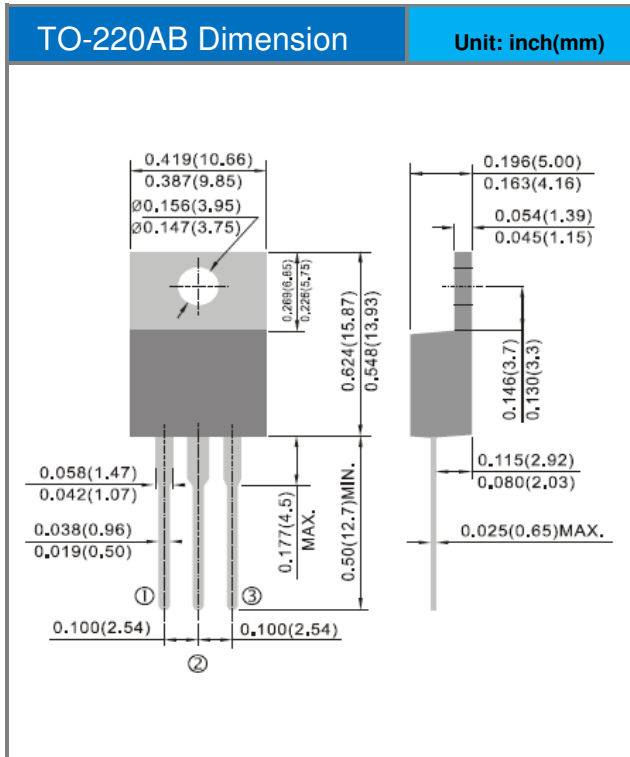


Fig.12 PJP100P03 Normalized Transient Thermal Impedance vs. Pulse Width



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Packaging Information





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PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJP100P03_T0_00001	TO-220AB	50pcs / Tube	P100P03	Halogen free



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